PAP49TJ43WJ

Dual P-Ch -20V Fast Switching MOSFET

V_{DS}=-20V, I_D=-9.0A ,$RDS_{(ON)}$=23mΩ

➢ General Description

This PAP49TJ43WJ Dual P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

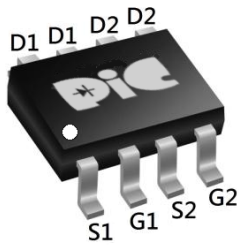
➢ Feature

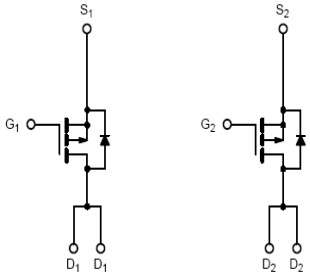
- ●100% EAS Guaranteed
- ●Green Device Available
- ●Super Low Gate Charge
- ●Excellent CdV/dt effect decline
- ●Advanced high cell density Trench technology
- ●SOP-8 package design

➢ Application

- ●Notebook CPU Core-High-Side Switch

➢ SOP-8





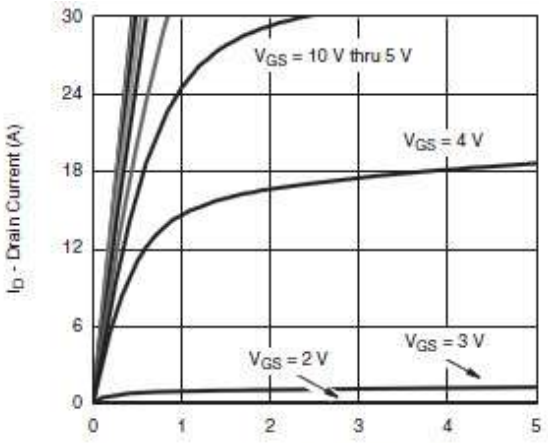
➢ Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-9.0	A
	T_A=70℃		-7.0	
Pulsed Drain Current		I_{DM}	-30	A
Continuous Source Current(Diode Conduction)	T_A=25℃	I_S	-1.7	A
Power Dissipation	T_A=25℃	P_D	2.8	W
	T_A=70℃		1.8	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	62.5	℃/W

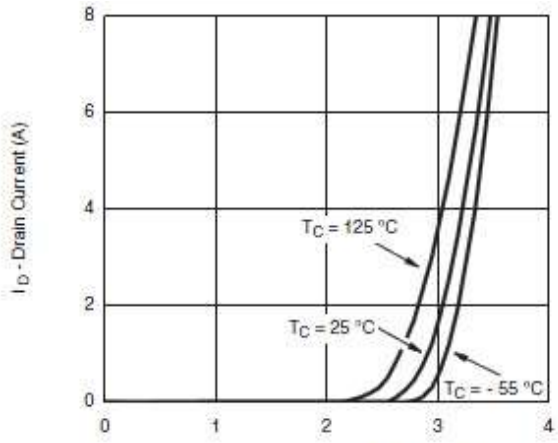
➢ Electrical Characteristics (T_J=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.4		-1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V,V_{GS}=0V			-1	uA
		V_{DS}=-16V,V_{GS}=0V T_J=85℃			-30	
On-State Drain Current	$I_{D(on)}$	V_{DS} = 5V,V_{GS}=-10V	-30			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-9.0A		18	23	mΩ
		V_{GS}=-2.5V,I_D=-7.0A		23	28	
		V_{GS}=-1.8V,I_D=-3.0A		30	35	
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-9.0A		22		S
Diode Forward Voltage	V_{SD}	I_S=-7.0A,V_{GS}=0V		-0.7	-1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-10V,V_{GS}=-4.5V I_D≡-7.0A		20	30	nC
Gate-Source Charge	Q_{gs}			6		
Gate-Drain Charge	Q_{gd}			10		
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V f=1MHz		1850		pF
Output Capacitance	C_{oss}			450		
Reverse Transfer Capacitance	C_{rss}			380		
Turn-On Time	$t_{d(on)}$	V_{DD}=-10V,R_L=1.5Ω I_D≡-7.0A,V_{GEN}=-10V R_G=1Ω		15	25	ns
	t_r			12	24	
Turn-Off Time	$t_{d(off)}$			35	55	
	t_f			10	20	

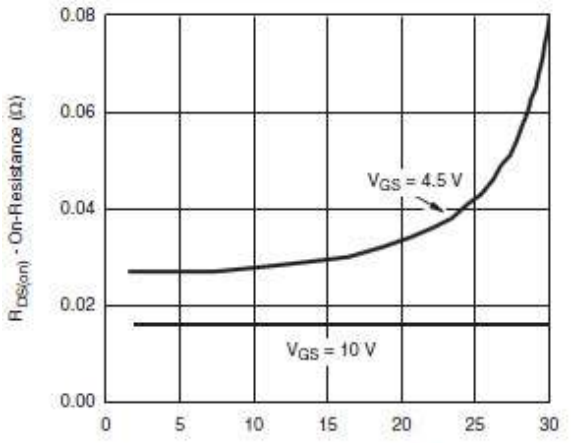
➢ Typical Characteristics



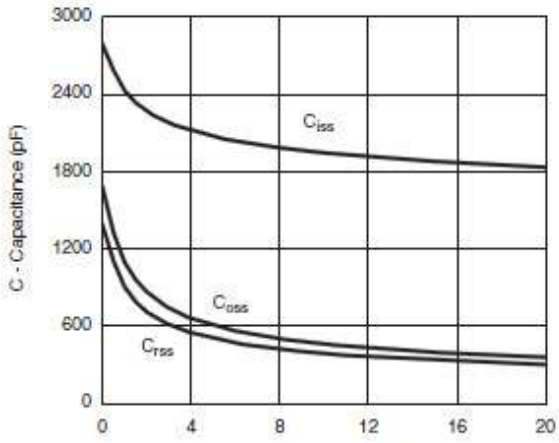
Output Characteristics



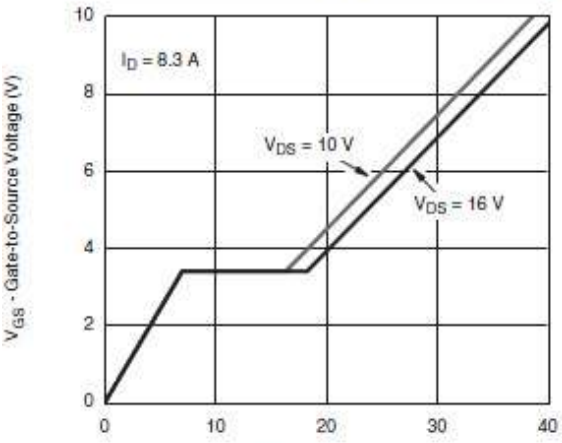
Transfer Characteristics



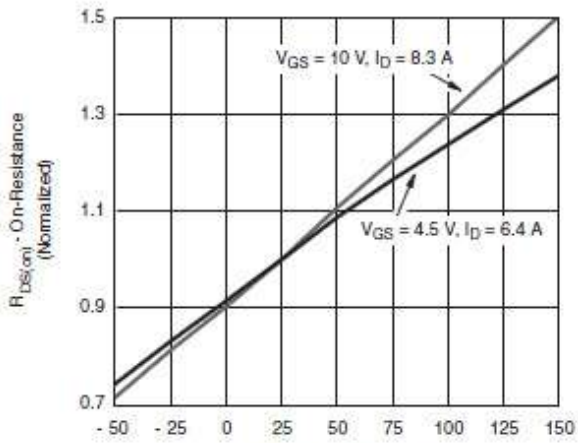
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

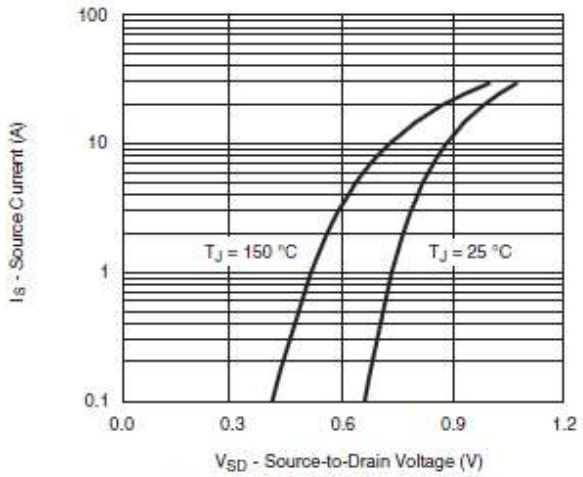


Gate Charge

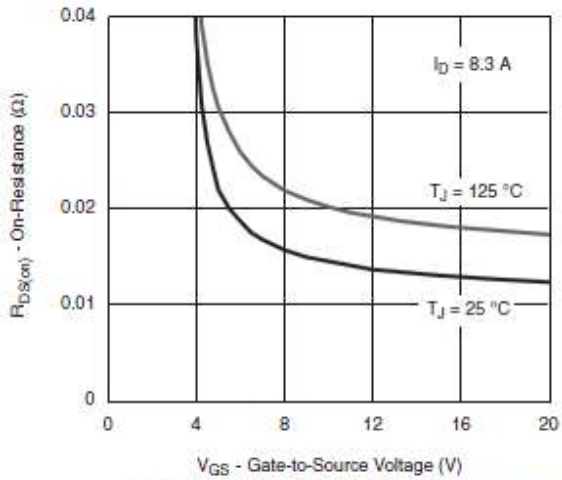


On-Resistance vs. Junction Temperature

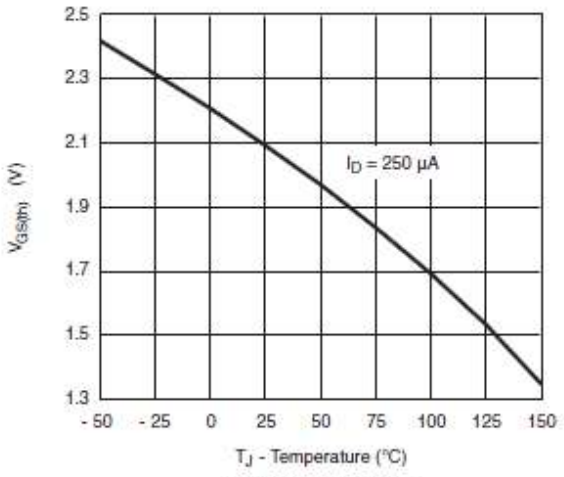
➢ Typical Characteristics



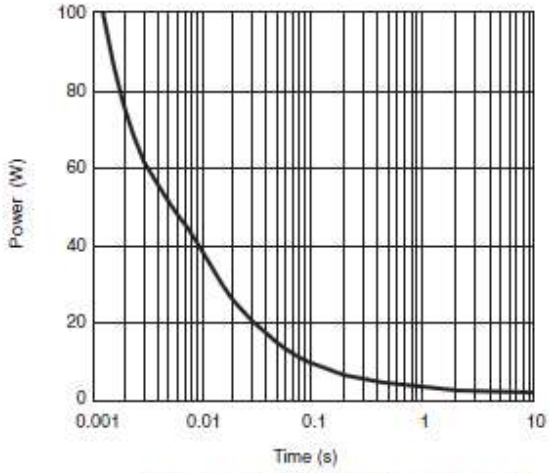
Source-Drain Diode Forward Voltage



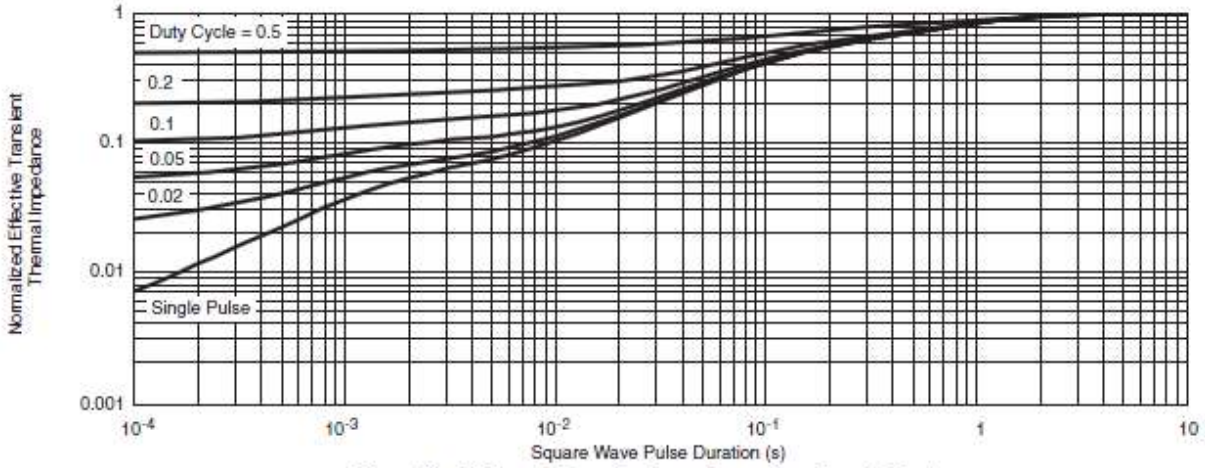
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

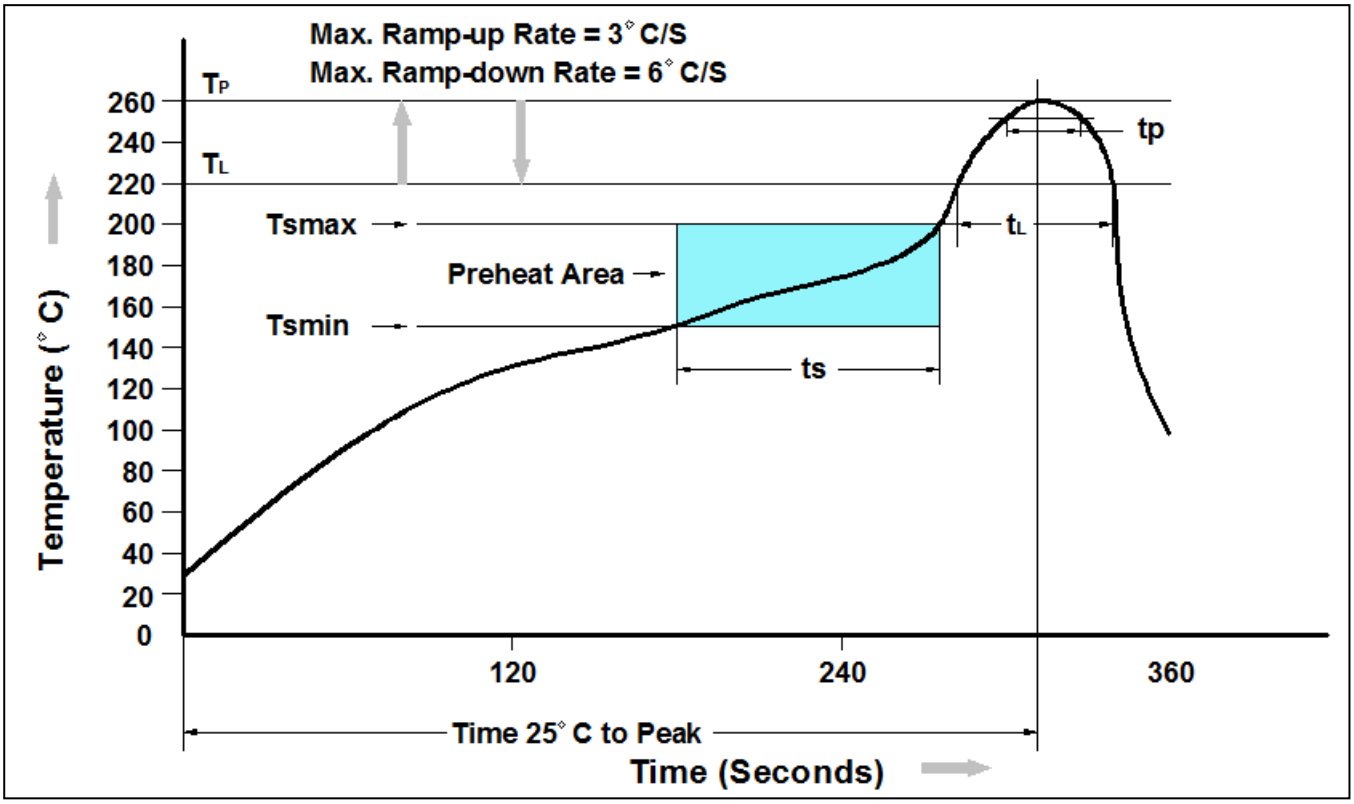


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

➢ Recommand IR Reflow Soldering Thermal Profile

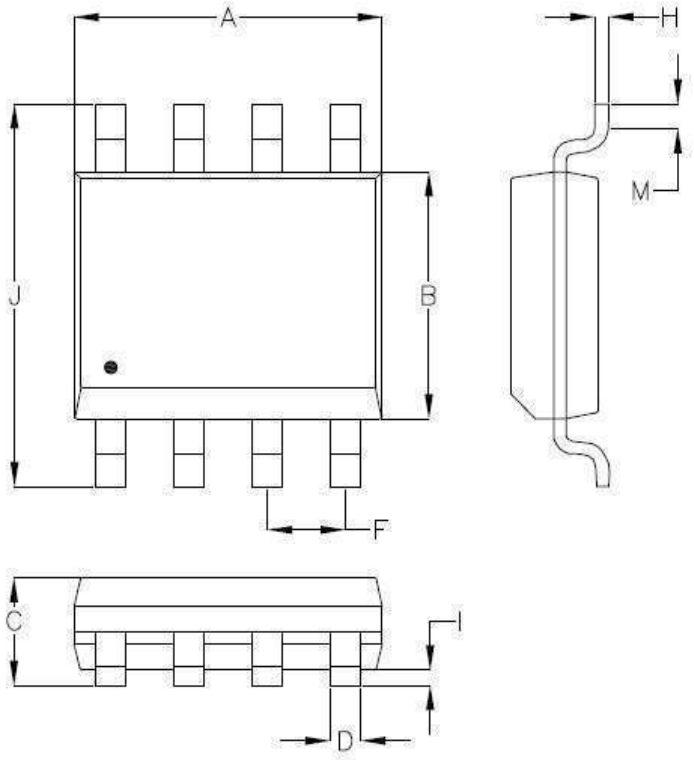


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAP49TJ43WJ	SOP-8 Reel	2500 pcs

➢ Package Information (SOP-8)



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.700	5.150	0.185	0.203
B	3.700	4.100	0.146	0.161
C	1.23	1.753	0.048	0.069
D	0.310	0.510	0.012	0.020
F	1.070	1.470	0.042	0.058
H	0.160	0.254	0.006	0.010
I	0.050	0.254	0.002	0.010
J	5.750	6.250	0.226	0.246
M	0.400	1.270	0.016	0.050

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